



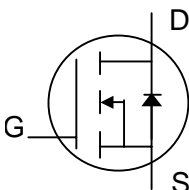
N-channel Enhancement-mode Power MOSFET

Simple Drive Requirement

Very Low On-resistance

Fast Switching Performance

RoHS-compliant, halogen-free



BV_{DS}	30V
$R_{DS(ON)}$	2.5m Ω
I_D	200A

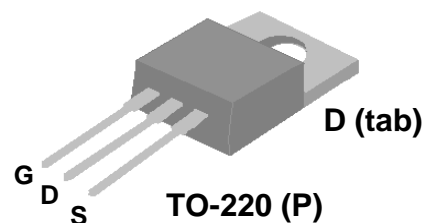
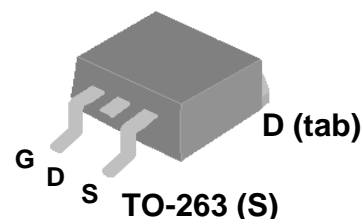
Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP99T03GS-HF-3 is in the TO-263 package, which is widely used for commercial and industrial surface-mount applications, and is well suited for low voltage applications such as DC/DC converters.

The AP99T03GP-HF-3 is in the TO-220 through-hole package which is used where a small PCB footprint or an attached heatsink is required.

Also available in the TO-262 surface mount package (AP99T03GR-HF-3) which is used when a small PCB footprint and long leads are required.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D at $T_C=25^\circ\text{C}$	Continuous Drain Current (Chip)	200	A
I_D at $T_C=25^\circ\text{C}$	Continuous Drain Current ³	120	A
I_D at $T_C=100^\circ\text{C}$	Continuous Drain Current ³	120	A
I_{DM}	Pulsed Drain Current ¹	800	A
P_D at $T_C=25^\circ\text{C}$	Total Power Dissipation	156	W
P_D at $T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	3.12	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	0.8	$^\circ\text{C/W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) ⁴	40	$^\circ\text{C/W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	$^\circ\text{C/W}$

Ordering Information

AP99T03GS-HF-3TR	RoHS-compliant TO-263, shipped on tape and reel (800 pcs/reel)
AP99T03GP-HF-3TB	RoHS-compliant TO-220, shipped in tubes (50pcs/tube, 1000pcs/box)
AP99T03GR-HF-3TB	RoHS-compliant TO-262, shipped in tubes (50pcs/tube, 1000pcs/box)



Electrical Specifications at $T_J=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=40A$	-	-	2.5	m Ω
		$V_{GS}=4.5V, I_D=30A$	-	-	4	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.8	-	2.5	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=30A$	-	110	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}= \pm 20V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge	$I_D=30A$	-	80	128	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=24V$	-	11.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	55	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V$	-	16	-	ns
t_r	Rise Time	$I_D=30A$	-	60	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	55	-	ns
t_f	Fall Time	$V_{GS}=10V$	-	20	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	5000	8000	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	1060	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	850	-	pF
R_g	Gate Resistance	$f=1.0\text{MHz}$	-	1.1	2.2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=40A, V_{GS}=0V$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$I_S=10A, V_{GS}=0V$	-	55	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	80	-	nC

Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse test
3. Package limitation current is 120A.
4. Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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Typical Electrical Characteristics

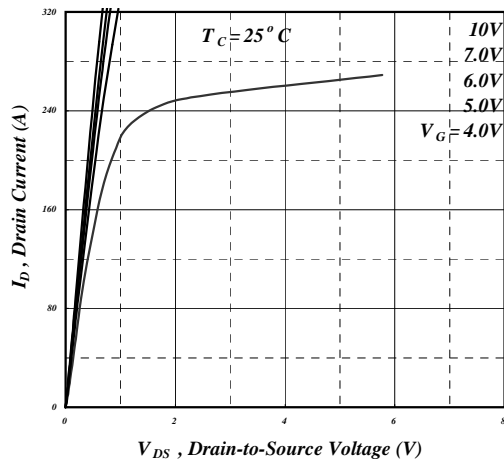


Fig 1. Typical Output Characteristics

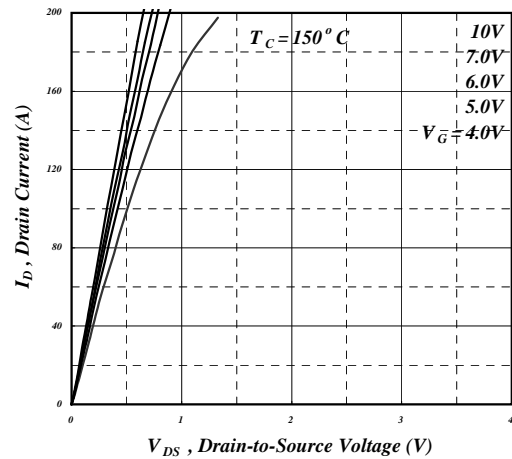


Fig 2. Typical Output Characteristics

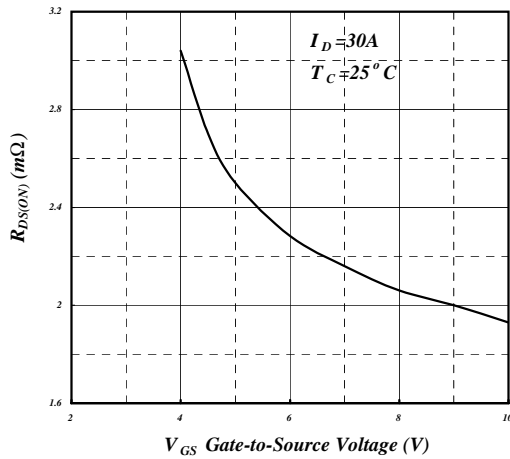


Fig 3. On-Resistance vs. Gate Voltage

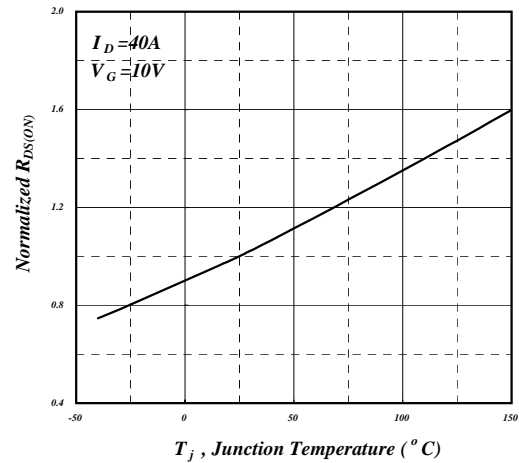


Fig 4. Normalized On-Resistance
vs. Junction Temperature

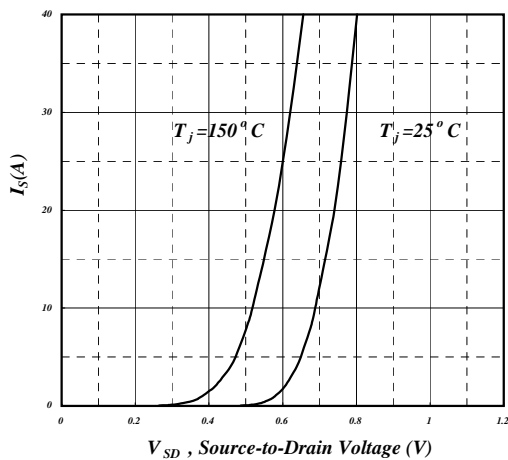


Fig 5. Forward Characteristic of
Reverse Diode

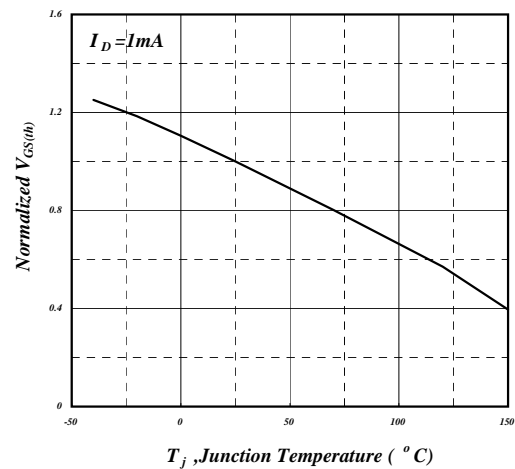


Fig 6. Gate Threshold Voltage vs.
Junction Temperature



Typical Electrical Characteristics (cont.)

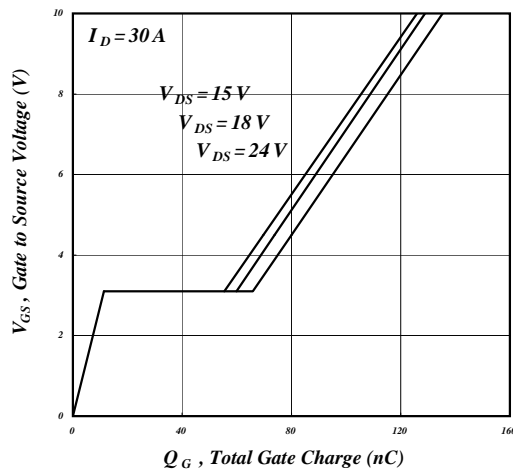


Fig 7. Gate Charge Characteristics

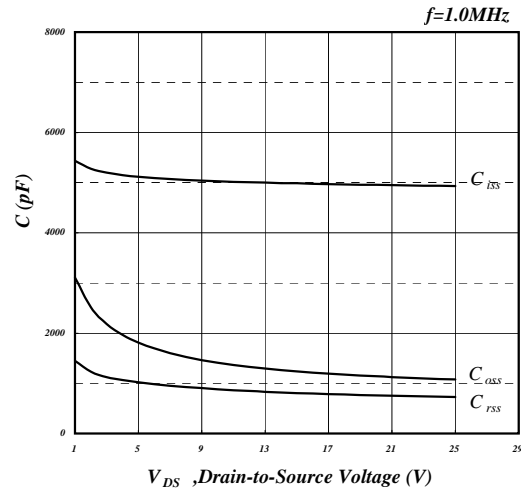


Fig 8. Typical Capacitance Characteristics

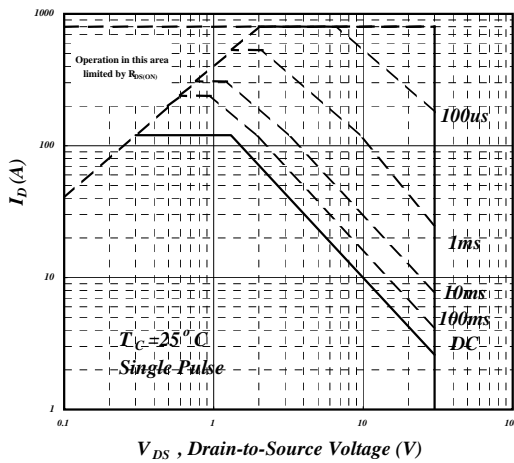


Fig 9. Maximum Safe Operating Area

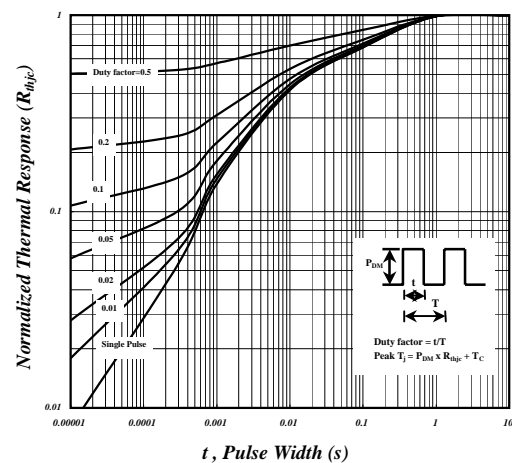


Fig 10. Effective Transient Thermal Impedance

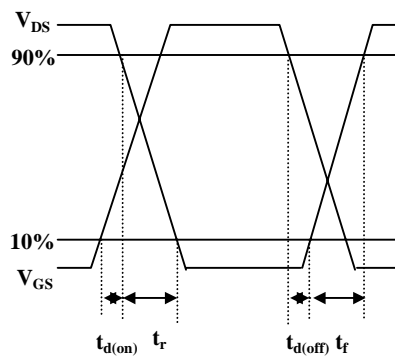


Fig 11. Switching Time Waveform

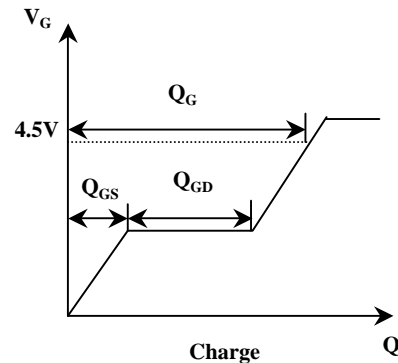
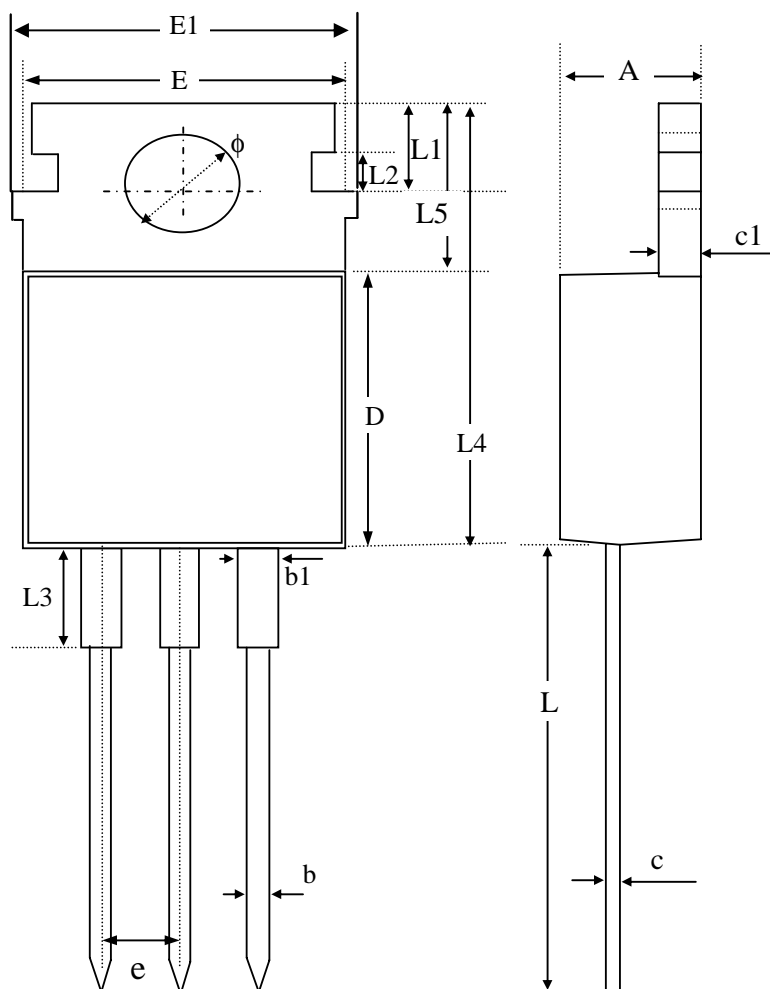


Fig 12. Gate Charge Waveform



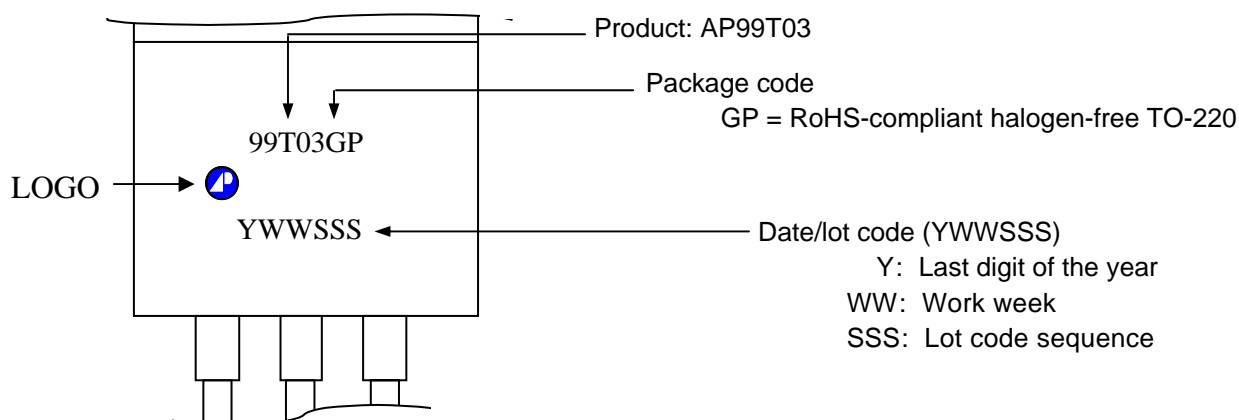
Package Dimensions: TO-220



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.25	4.48	4.70
b	0.65	0.80	0.90
b1	1.15	1.38	1.60
c	0.40	0.50	0.60
c1	1.00	1.20	1.40
E	9.70	10.00	10.40
E1	---	---	11.50
e	---	2.54	---
L	12.70	13.60	14.50
L1	2.60	2.80	3.00
L2	1.00	1.40	1.80
L3	2.6	3.10	3.6
L4	14.70	15.50	16
L5	6.30	6.50	6.70
ϕ	3.50	3.60	3.70
D	8.40	8.90	9.40

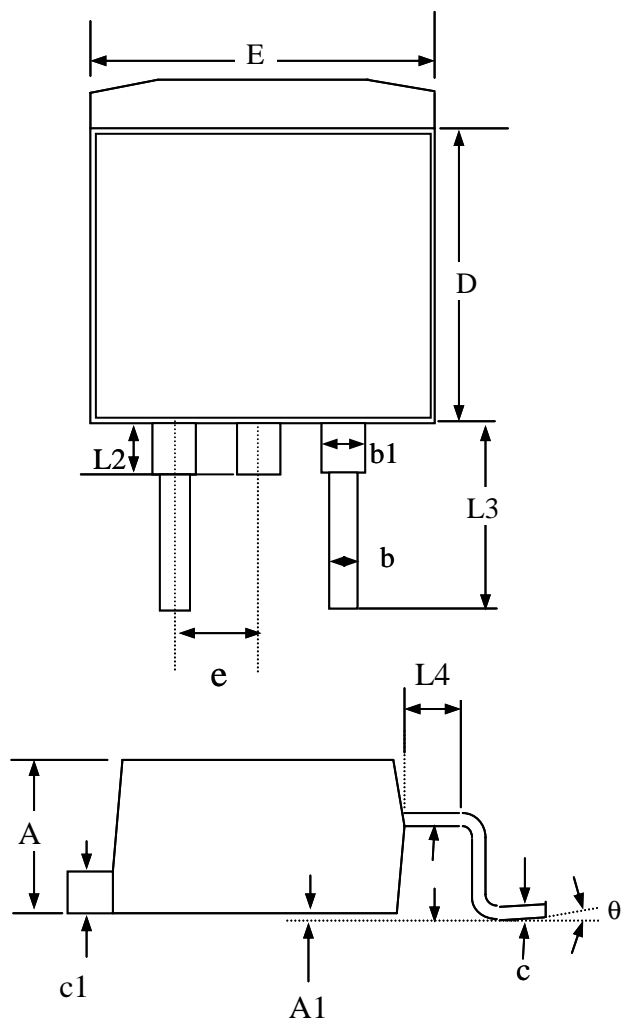
1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information: TO-220





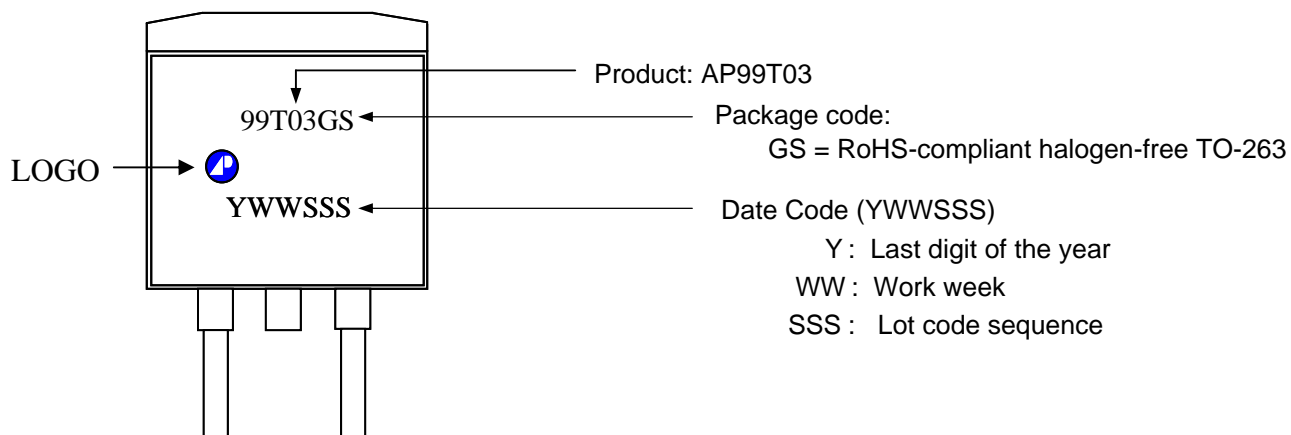
Package Dimensions: TO-263



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.25	4.75	5.20
A1	0.00	0.15	0.30
A2	2.20	2.45	2.70
b	0.70	0.90	1.10
b1	1.07	1.27	1.47
c	0.30	0.45	0.60
c1	1.15	1.30	1.45
D	8.30	8.90	9.40
E	9.70	10.10	10.50
e	2.04	2.54	3.04
L2	-----	1.50	-----
L3	4.50	4.90	5.30
L4	-----	1.50	----

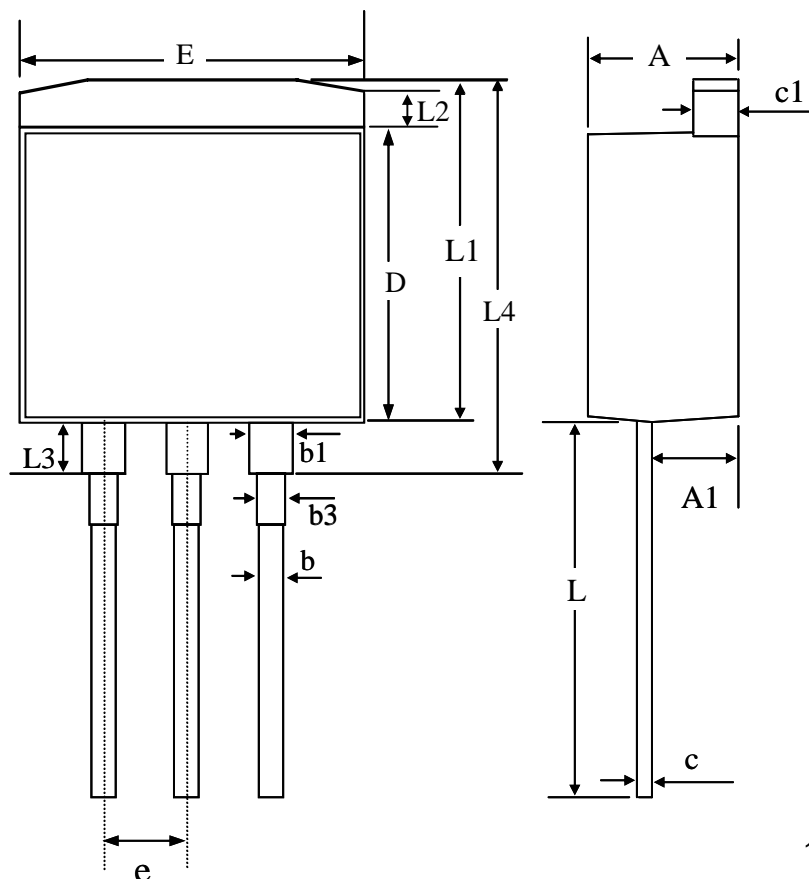
1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information: TO-263





Package Dimensions: TO-262



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.24	4.44	4.64
A1	-----	-----	2.70
b	0.66	0.76	0.86
b1	1.07	1.27	1.47
b3	0.76	0.86	1.06
c	0.30	0.40	0.50
c1	1.15	1.30	1.45
D	8.30	8.60	8.90
E	9.90	10.20	10.50
e	2.04	2.54	3.04
L	10.50	11.00	11.50
L1	9.50	10.00	10.30
L3	----	1.30	----
L4	10.80	11.30	11.35

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information: TO-262

